

YJ



■ **Electrical Characteristics** ($T_J=25$ unless otherwise noted)

Typical Performance Characteristics

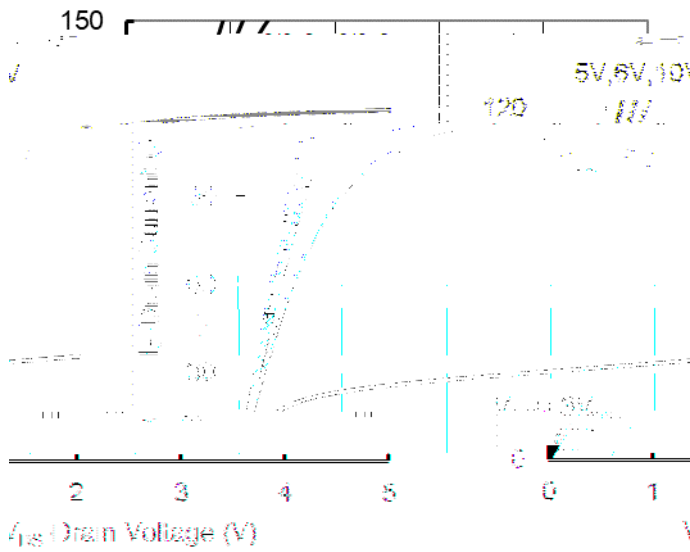


Figure 1. Output Characteristics

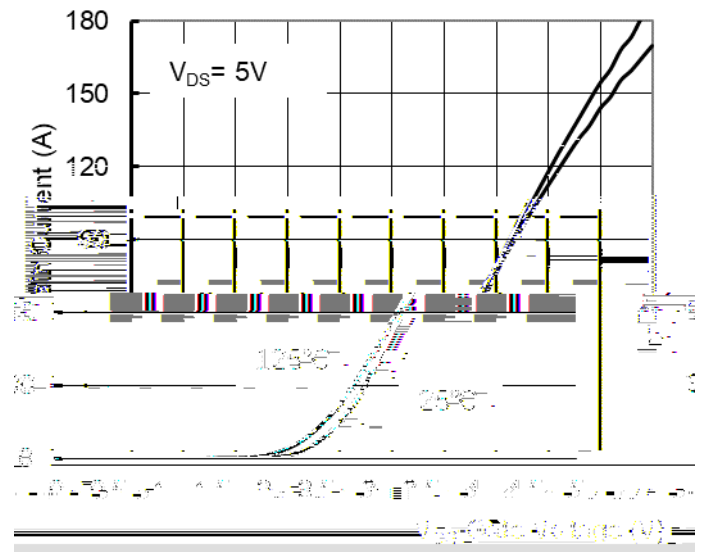


Figure 2. Transfer Characteristics

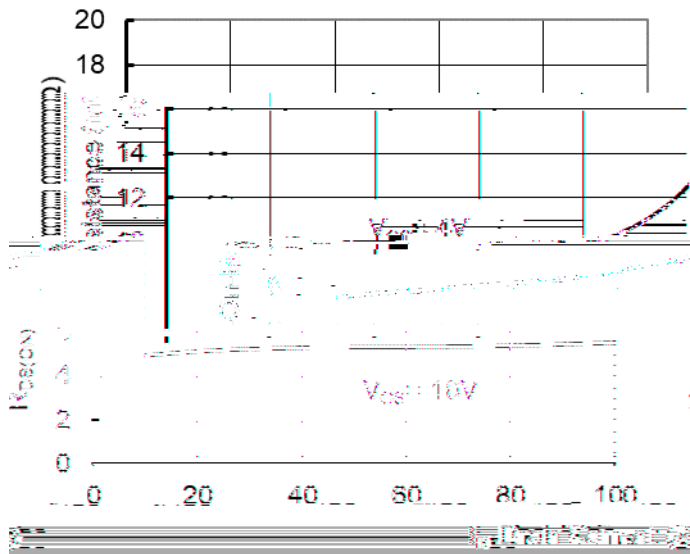


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

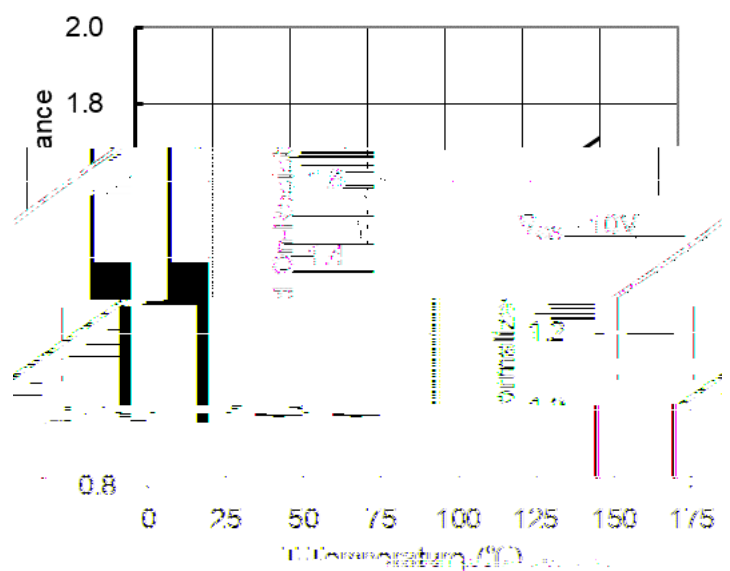


Figure 4. On-Resistance vs. Junction Temperature

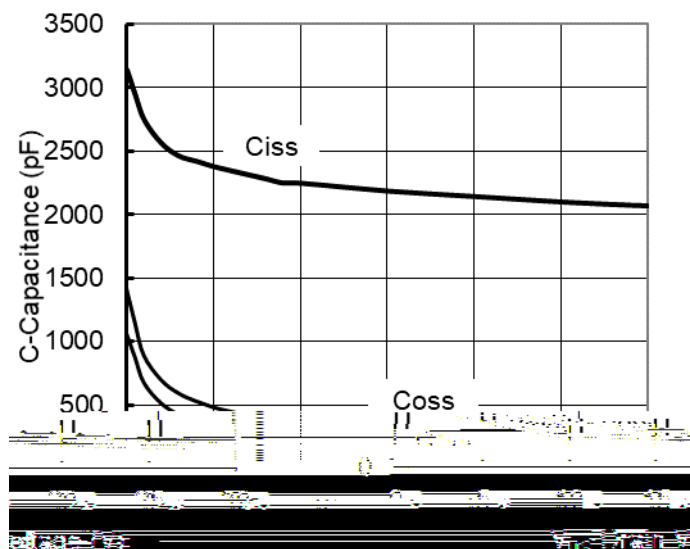


Figure 5. Capacitance Characteristics

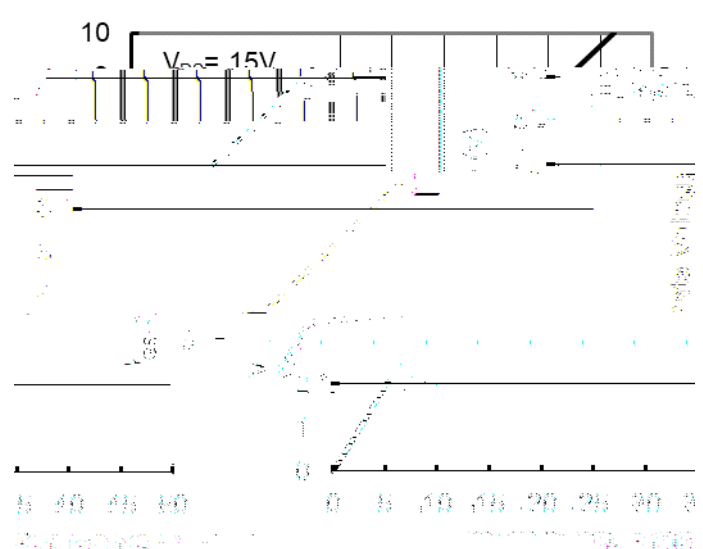


Figure 6. Gate Charge

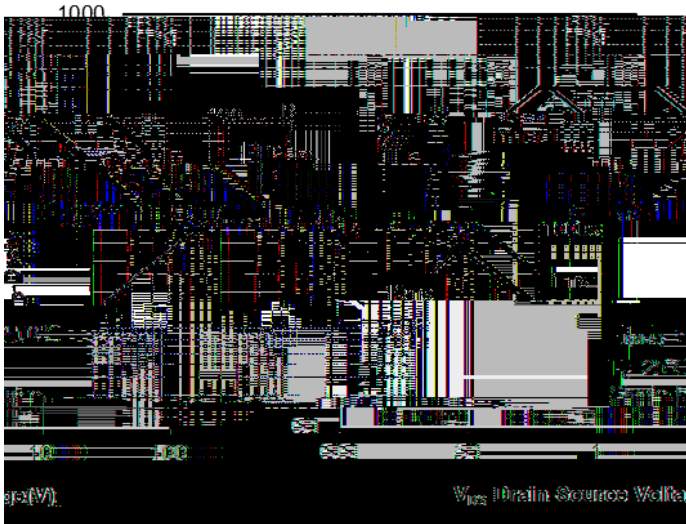
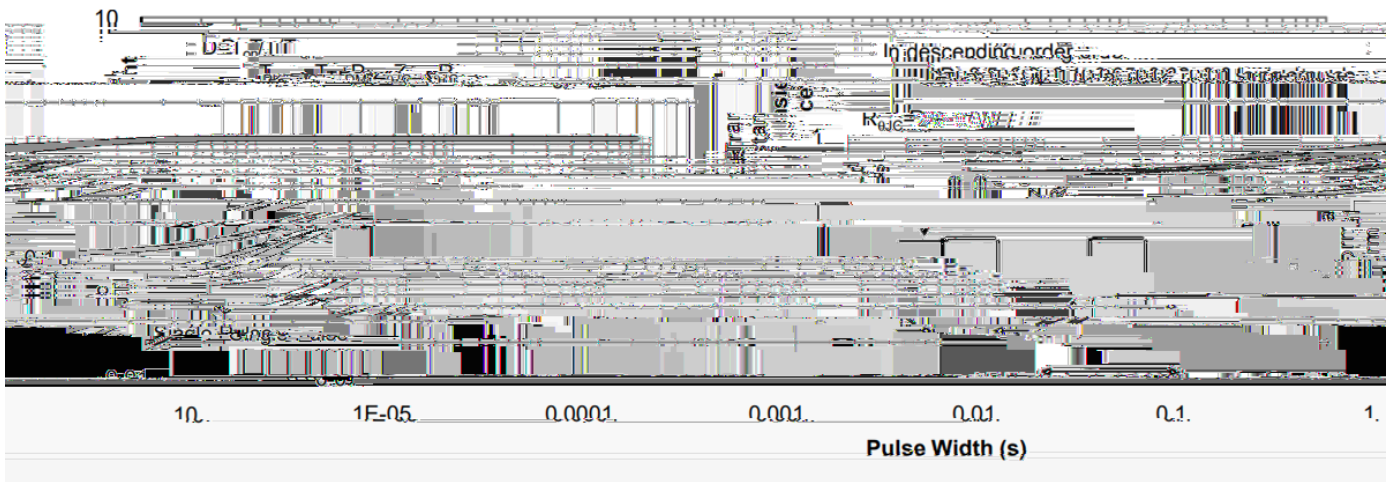
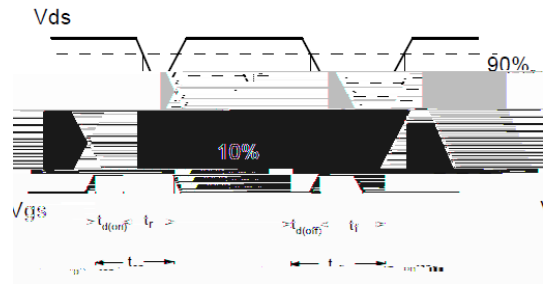
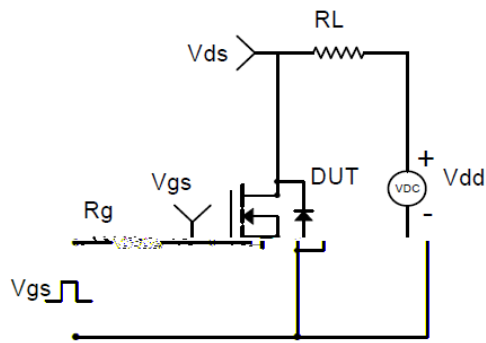


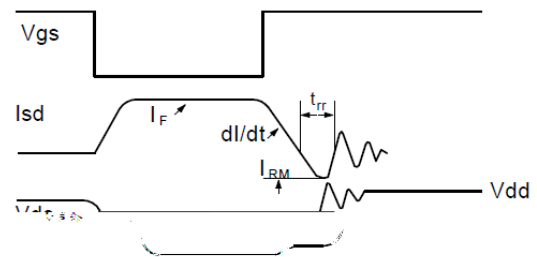
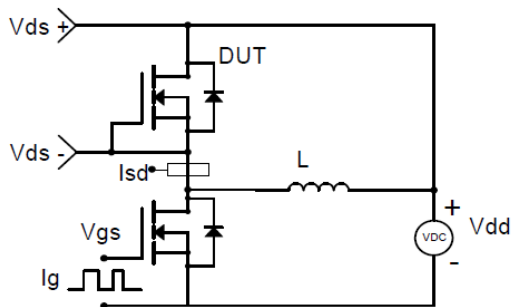
Figure 7. Safe Operation Area

Figure 8. Maximum Continuous Drain Current vs Case Temperature

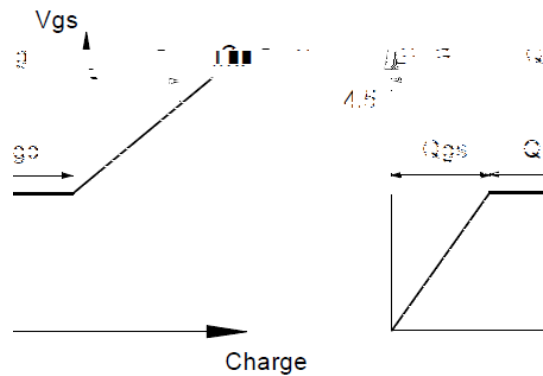
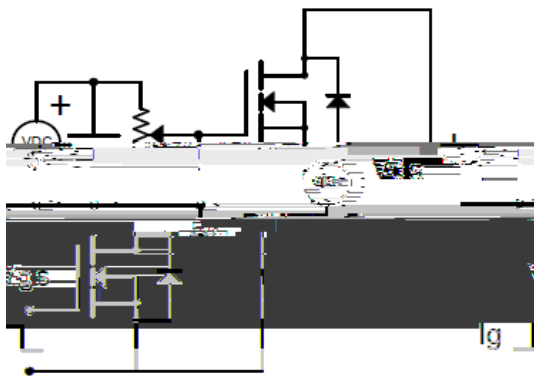




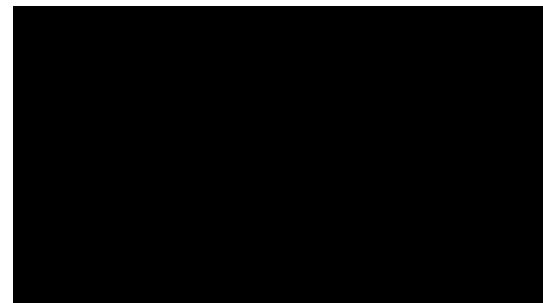
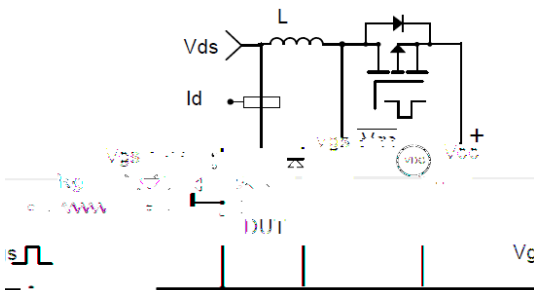
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



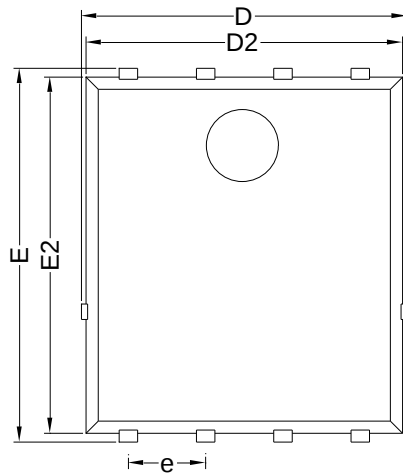
Gate Charge Test Circuit & Waveform



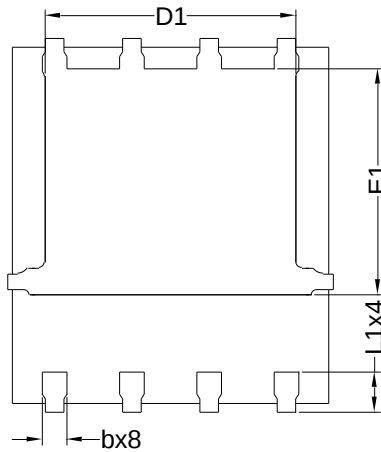
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



■ PDFN5060-8L-B-1.1MM Package Information



Top View



Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



Disclaimer

The QeQ2Th10p1(T0 n[rTf1 -Qq3 0 15)11(T)6n6(h10.)5(2)p[rT-QG[sG[nq3 0 (T0 G[dh10.)5(2)11(T)6(h10.)5(2)0 15)0 11(T)6s)260.)5(2)dh10